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Monte Carlo calculations of keV electron and positron slowing down in solids. II

DOI: 10.1007/bf00620300

Applied Physics A: Solids and Surfaces, 1984, 35, 51-59.

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#	Paper	IF	Citations
227	Measurement of positron reemission from thin single-crystal W(100) films. <i>Physical Review B</i> , 1985 , 31, 4123-4130	3.3	88
226	Cylinder radioactive source for slow-positron beams. 1985 , 56, 1531-1533		8
225	Observation of electron transport in polyethylene terephthalate and the radiation hardening of dielectrics. 1985 , 46, 1105-1107		5
224	Positron diffusion in Si. <i>Physical Review B</i> , 1985 , 32, 2296-2301	3.3	69
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